TOSHIBA Photocoupler GaAs Ired & Photo-Transistor

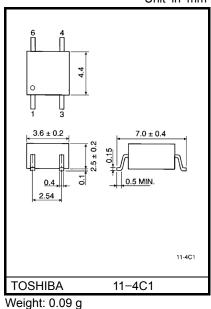
# **TLP180**

Programmable Controllers AC / DC–Input Module Telecommunication

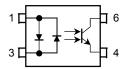
The TOSHIBA mini flat coupler TLP180 is a small outline coupler, suitable for surface mount assembly.

TLP180 consist of a photo transistor, optically coupled to a gallium arsenide infrared emitting diode connected inverse parallel, and can operate directly by AC input current.

- Collector-emitter voltage: 80 V (min.)
- Current transfer ratio: 50% (min.) Rank GB: 100% (min.)
- Isolation voltage: 3750Vrms (min.)
- UL recognized: UL1577, file No. E67349
- BSI approved: BS EN60065:2002, certificate no.8285 BS EN60950-1:2002, certificate no.8286



### Pin Configuration (top view)



1: Anode, Cathode

- 3: Cathode, Anode
- 4: Emitter
- 6: Collector

Unit in mm

Absolute Maximum Ratings (Ta = 25°C)

	Characteristic	Symbol	Rating	Unit
D	Forward current	I <sub>F(RMS)</sub>	±50	mA
	Forward current detating (Ta≥53°C)	ΔI <sub>F</sub> / °C	-0.7	mA / °C
LED	Pulse forward current (Note1)	I <sub>FP</sub>	±1	A
	Junction temperature	Tj	125	°C
	Collector-emitter voltage	V <sub>CEO</sub>	80	V
	Emitter-collector voltage	V <sub>ECO</sub>	7	V
ctor	Collector current	Ι <sub>C</sub>	50	mA
Detector	Power dissipation	P <sub>C</sub>	150	mW
	Power dissipation derating (Ta ≥ 25°C)	ΔP <sub>C</sub> / °C	-1.5	mW / °C
	Junction temperature	Tj	125	°C
Stor	age temperature range	T <sub>stg</sub>	-55~125	°C
Ope	erating temperature range	T <sub>opr</sub>	-55~100	°C
Lea	d soldering temperature(10s)	T <sub>sol</sub>	260	°C
Tota	al package power dissipation	PT	200	mW
Tota	al package power dissipation derating (Ta $\ge$ 25°C)	ΔP <sub>T</sub> / °C	-2.0	mW / °C
Isola	ation voltage (AC,1min.,R.H. ≤ 60%) (Note 2)	BVS	3750	Vrms

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Pulse width ≤ 100µs,f=100Hz

Note 2: Device considered a two terminal device: Pins 1 and 3 shorted together and 4 and 6 shorted together.

## **Recommended Operating Conditions**

Characteristic	Symbol	Min.	Тур.	Max.	Unit
Supply voltage	V <sub>CC</sub>	_	5	48	V
Forward current	I <sub>F(RMS)</sub>	—	16	20	mA
Collector current	IC	—	1	10	mA
Operating temperature	T <sub>opr</sub>	-25		85	°C

Note: Recommended operating conditions are given as a design guideline to obtain expected performance of the device. Additionally, each item is an independent guideline respectively. In developing designs using this product, please confirm specified characteristics shown in this document.

**Electrical Characteristics (Ta = 25°C)** 

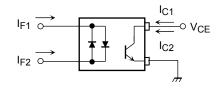
	Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
LED	Forward voltage	VF	I <sub>F</sub> = ±10 mA	1.0	1.15	1.3	V
Ш	Capacitance	CT	V = 0, f = 1 MHz	_	60	_	pF
	Collector–emitter breakdown voltage	V <sub>(BR)</sub> CEO	I <sub>C</sub> = 0.5 mA	80	_	_	V
Detector	Emitter–collector breakdown voltage	V <sub>(BR) ECO</sub>	I <sub>E</sub> = 0.1 mA	7	_	_	V
	Collector dark current		V <sub>CE</sub> = 48 V (ambient light below 1000Lx) (Note3)	_	0.01 (2)	0.1 (10)	μA
		ICEO	V <sub>CE</sub> = 48 V (ambient light Ta = 85°C below 1000Lx) (Note3)	_	2 (4)	50 (50)	μA
	Capacitance (collector to emitter)	C <sub>CE</sub>	V = 0, f = 1 MHz		10		pF

Note 3: Please use standard electric lamp to light up the device's marking surface.

## **Coupled Electrical Characteristics (Ta = 25°C)**

Characteristic	Symbol	Test Condition	Mln.	Тур.	Max.	Unit
Current transfer ratio	IC / IF	I <sub>F</sub> = ±5 mA, V <sub>CE</sub> = 5 V	50	_	600	%
	1C / 1F	Rank GB	100	_	600	70
Saturated CTR $I_C / I_F (sat)$ $I_F = \pm 1 m/$	IF = ±1 mA, V <sub>CE</sub> = 0.4 V	_	60	_	%	
	IC / IF (sat)	Rank GB	30	_	_	-70
	V <sub>CE (sat)</sub>	I <sub>C</sub> = 2.4 mA, I <sub>F</sub> = ±8 mA	-	_	0.4	
Collector–emitter saturation voltage		$I_{C}$ = 0.2 mA, $I_{F}$ = ±1 mA Rank GB	_	0.2	_	V
			-	_	0.4	
Off-state collector current	I <sub>C(off)</sub>	V <sub>F</sub> = ± 0.7V, V <sub>CE</sub> = 48 V	_	1	10	μA
CTR symmetry	I <sub>C (ratio)</sub>	$I_C (I_F = -5mA) / I_C (I_F = 5mA)$ (Note4)	0.33	1	3	_

Note 4 :  $I_C(ratio) = \frac{I_{C2}(I_F = I_{F2}, V_{CE} = 5V)}{I_{C1}(I_F = I_{F1}, V_{CE} = 5V)}$ 



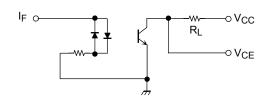
Isolation Characteristics (Ta = 25°C)

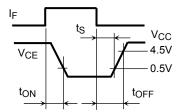
Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Capacitance input to output	CS	V <sub>S</sub> = 0V, f = 1 MHz	_	0.8	_	pF
Isolation resistance	R <sub>S</sub>	V <sub>S</sub> = 500 V, R.H. ≤ 60%	5×10 <sup>10</sup>	10 <sup>14</sup>	_	Ω
		AC, 1 minute	3750	_	_	V
Isolation voltage	BVS	AC, 1 second, in oil	_	10000	_	V <sub>rms</sub>
		DC, 1 minute, in oil	_	10000	-	V <sub>dc</sub>

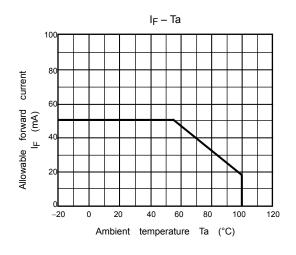
## Switching Characteristics (Ta = 25°C)

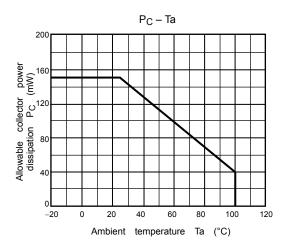
Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Rise time	t <sub>r</sub>	V <sub>CC</sub> = 10 V, I <sub>C</sub> = 2 mA R <sub>L</sub> = 100Ω	_	2	_	
Fall time	t <sub>f</sub>		_	3	_	μs
Turn–on time	t <sub>on</sub>		_	3	_	
Turn–off time	t <sub>off</sub>		_	3	_	
Turn–on time	t <sub>ON</sub>		_	2	_	
Storage time	ts	$\begin{array}{l} R_{L} = 1.9 \; k\Omega \qquad (Fig.1) \\ V_{CC} = 5 \; V, \; I_{F} = \pm 16 \; mA \end{array}$	_	25	_	μs
Turn-off time	tOFF		_	40	_	

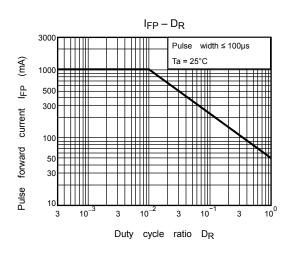
Fig. 1: Switching time test circuit

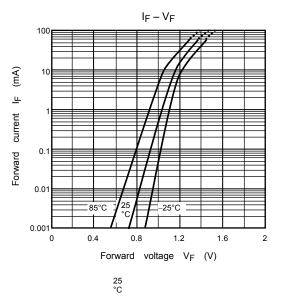


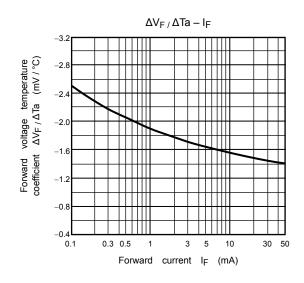




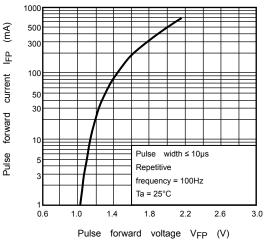


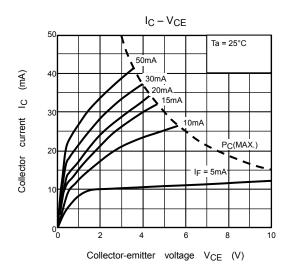


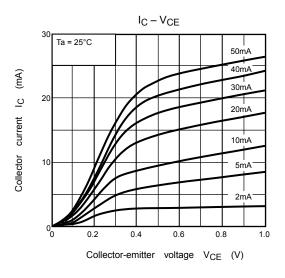


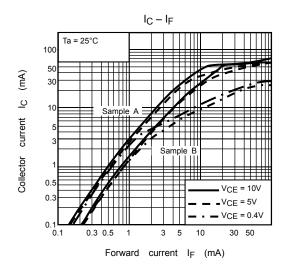


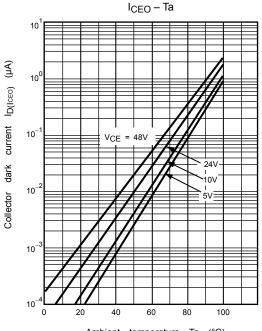
 $I_{\rm FP} - V_{\rm FP}$ 



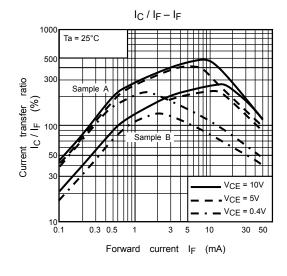


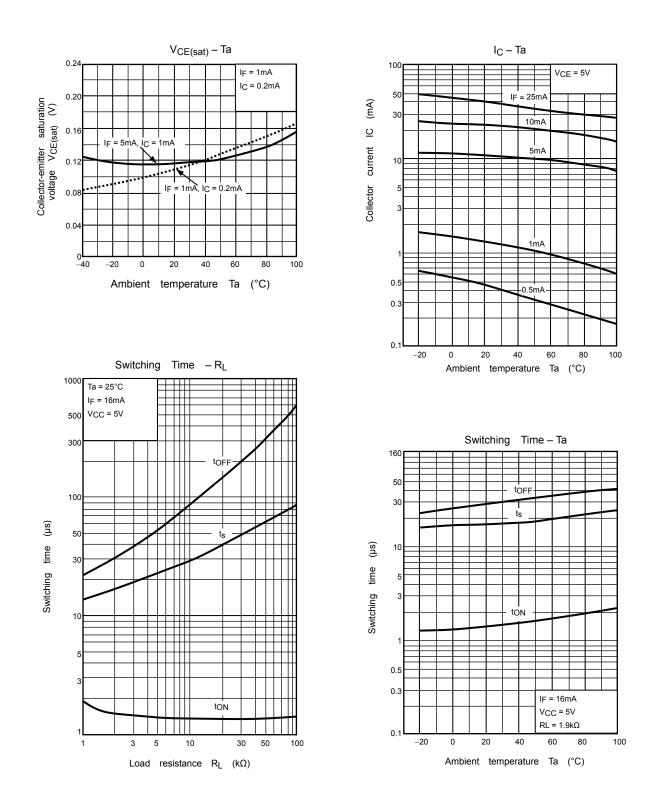






Ambient temperature Ta (°C)





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